

January 22, 2004

To: Commissioner for Patents  
P.O.Box 1450  
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/718,193 11/20/03 |

Zheng Jia Zhen et al.

A METHOD TO ENHANCE INDUCTOR Q  
FACTOR BY FORMING AIR GAPS BELOW  
INDUCTORS

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56.

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
mail in an envelope addressed to: Commissioner for Patents,  
P.O. Box 1450, Alexandria, VA 22313-1450, on January 27, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 1/27/04

U.S. Patent 6,180,995 to Hebert, "Integrated Passive Devices with Reduced Parasitic Substrate Capacitance," describes an air gap under a field oxide under inductors.

U.S. Patent 6,307,247 to Davies, "Monolithic Low Dielectric Constant Platform for Passive Components and Method," describes an inductor process with low-k layers.

U.S. Patent 6,287,979 to Zhou et al., "Method for Forming an Air Gap as Low Dielectric Constant Material Using Buckminsterfullerene as a Porogen in an Air Bridge or a Sacrificial Layer," describes an air gap process between conductive lines.

U.S. Patent 5,742,091 to Hebert, "Semiconductor Device Having a Passive Device Formed Over One or More Deep Trenches," describes a semiconductor device within which parasitic capacitances are minimized and a method of fabricating same.

U.S. Patent 6,303,423 to Lin, "Method for Forming High Performance System-On-Chip Using Post Passivation Process," describes a method for forming high performance system-on-chip using post passivation process.

CS-01-140

U.S. Patent 4,634,494 to Taji et al., "Etching of a Phosphosilicate Glass Film Selectively Implanted with Boron," describes a process to selectively etch a doped oxide layer.

Sincerely,

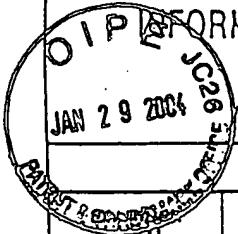


Stephen B. Ackerman,  
Reg. No. 37761

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O P E RATION DISCLOSURE CITATION  
IN AN APPLICATION

JAN 29 2004 <sup>as</sup> (Use several sheets if necessary)

CS-01-140

10/718, 193

AppIcon

Zheng Jia-Zhen et al.

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Group A1 Unit

## U. S. PATENT DOCUMENTS

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

**OTHER DOCUMENTS** (Including Author, Title, Date, Portion or Pages, Etc.)


DUMMER

**DATE CONSIDERED**

**EXAMINER:** Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.



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ASSOCIATE POWER OF ATTORNEY

I hereby appoint Stephen G. Stanton, registration number 35,690, as my associate attorney in this case. His telephone number is (610) 296-5194.

Please continue to direct all correspondence in this case to the undersigned attorney.

Respectfully submitted,

Stephen B. Ackerman,

Principal attorney of record